**intersil**®

## EL2126

Data Sheet

April 16, 2007

FN7046.3

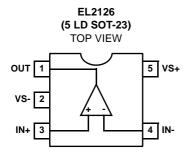
# Ultra-Low Noise, Low Power, Wideband Amplifier

The EL2126 is an ultra-low noise, wideband amplifier that runs on half the supply current of competitive parts. It is intended for use in systems such as ultrasound imaging where a very small signal needs to be amplified by a large amount without adding significant noise. Its low power dissipation enables it to be packaged in the tiny SOT-23 package, which further helps systems where many input channels create both space and power dissipation problems.

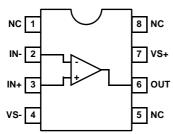
The EL2126 is stable for gains of 10 and greater and uses traditional voltage feedback. This allows the use of reactive elements in the feedback loop, a common requirement for many filter topologies. It operates from  $\pm 2.5$ V to  $\pm 15$ V supplies and is available in the 5 Ld SOT-23 and 8 Ld SO packages.

The EL2126 is fabricated in Elantec's proprietary complementary bipolar process, and is specified for operation over the full -40°C to +85°C temperature range.

## **Pinouts**







## Features

- Voltage noise of only 1.3nV/÷Hz
- Current noise of only 1.2pA/÷Hz
- 200µV offset voltage
- 100MHz -3dB BW for  $A_V = 10$
- Very low supply current 4.7mA
- SOT-23 package
- ±2.5V to ±15V operation
- Pb-free plus anneal available (RoHS compliant)

## Applications

- Ultrasound input amplifiers
- Wideband instrumentation
- Communication equipment
- AGC & PLL active filters
- Wideband sensors

## **Ordering Information**

Part Number	PART MARKING	TEMP RANGE (°c)	Tape & Reel	Package	pkg. dWG. #
EL2126CW-T7	G	-40 to +85	7" (3K pcs)	5 Ld SOT-23	MDP0038
EL2126CW-T7A	G	-40 to +85	7" (250 pcs)	5 Ld SOT-23	MDP0038
EL2126CS	2126CS	-40 to +85	-	8 Ld SOIC	MDP0027
EL2126CS-T7	2126CS	-40 to +85	7"	8 Ld SOIC	MDP0027
EL2126CS-T13	2126CS	-40 to +85	13"	8 Ld SOIC	MDP0027
EL2126CSZ ( Note)	2126CSZ	-40 to +85	-	8 Ld SOIC (Pb-free)	MDP0027
EL2126CSZ-T7 ( Note)	2126CSZ	-40 to +85	7"	8 Ld SOIC (Pb-free)	MDP0027
EL2126CSZ-T13 (Note)	2126CSZ	-40 to +85	13"	8 Ld SOIC (Pb-free)	MDP0027
EL2126CWZ-T7 (Note)	ВААН	-40 to +85	7"	5 Ld SOT-23	P5.064
EL2126CWZ-T7A (Note)	ВААН	-40 to +85	7"	5 Ld SOT-23	P5.064

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

#### **Absolute Maximum Ratings**

V <sub>S</sub> + to V <sub>S</sub> -)	
Continuous Output Current 40mA	
Any Input	

#### **Thermal Information**

Operating Temperature4	0°C to +85°C
Storage Temperature60	°C to +150°C
Maximum Die Junction Temperature	+150°C
Power Dissipation	. See Curves
Pb-free reflow profiles	ee link below
http://www.intersil.com/pbfree/Pb-FreeReflow.asp	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typical values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore:  $T_J = T_C = T_A$ 

Parameter	Description	Conditions	Min	Тур	Мах	Unit
DC PERFORM	IANCE	•	-	+		-
V <sub>OS</sub>	Input Offset Voltage (SO8)			0.2	2	mV
	Input Offset Voltage (SOT23-5)				3	mV
T <sub>CVOS</sub>	Offset Voltage Temperature Coefficient			17		µV/°C
I <sub>B</sub>	Input Bias Current		-10	-7		μA
I <sub>OS</sub>	Input Bias Current Offset			0.06	0.6	μA
T <sub>CIB</sub>	Input Bias Current Temperature Coefficient			0.013		µA/°C
C <sub>IN</sub>	Input Capacitance			2.2		pF
A <sub>VOL</sub>	Open Loop Gain	V <sub>O</sub> = -2.5V to +2.5V	80	87		dB
PSRR	Power Supply Rejection Ratio (Note 1)		80	100		dB
CMRR	Common Mode Rejection Ratio	at CMIR	75	106		dB
CMIR	Common Mode Input Range		-4.6		3.8	V
V <sub>OUTH</sub>	Positive Output Voltage Swing	No load, $R_F = 1k\Omega$	3.8	3.8		V
V <sub>OUTL</sub>	Negative Output Voltage Swing	No load, $R_F = 1k\Omega$		-4	-3.9	V
V <sub>OUTH2</sub>	Positive Output Voltage Swing	R <sub>L</sub> = 100Ω	3.2	3.45		V
V <sub>OUTL2</sub>	Negative Output Voltage Swing	R <sub>L</sub> = 100Ω		-3.5	-3.2	V
IOUT	Output Short Circuit Current (Note 2)		80	100		mA
I <sub>SY</sub>	Supply Current			4.7	5.5	mA
AC PERFORM	IANCE - R <sub>G</sub> = 20Ω, C <sub>L</sub> = 3pF					
BW	-3dB Bandwidth, $R_L = 500\Omega$			100		MHz
BW ±0.1dB	±0.1dB Bandwidth, $R_L = 500\Omega$			17		MHz
BW ±1dB	$\pm 1$ dB Bandwidth, R <sub>L</sub> = 500 $\Omega$			80		MHz
Peaking	Peaking, $R_L = 500\Omega$			0.6		dB
SR	Slew Rate	$V_{OUT} = 2V_{P-P}$ , measured at 20% to 80%	80	110		V/µs
OS	Overshoot, 4V <sub>P-P</sub> Output Square	Positive		2.8		%
	Wave	Negative		-7		%
ts	Settling Time to 0.1% of ±1V Pulse			51		ns

## $\label{eq:expectations} Electrical Specifications \qquad \forall_{S}\texttt{+}=\texttt{+}5\forall, \ \forall_{S}\texttt{-}=\texttt{-}5\forall, \ \mathsf{T}_{A}=\texttt{+}25^{\circ}\texttt{C}, \ \mathsf{R}_{F}=\texttt{1}80\Omega, \ \mathsf{R}_{G}=\texttt{2}0\Omega, \ \mathsf{R}_{L}=\texttt{5}00\Omega \ \text{unless otherwise specified}.$

## EL2126

<b>Electrical Specifications</b> $V_{S}$ + = +5V, $V_{S}$ - = -5V, $T_{A}$ = +25°C, $R_{F}$ = 180 $\Omega$ , $R_{G}$ = 20 $\Omega$ , $R_{L}$ = 500 $\Omega$ unless otherwise specified. (Continued)									
Parameter	Description	Conditions	Min	Тур	Max	Unit			
V <sub>N</sub>	Voltage Noise Spectral Density			1.3		nV/√Hz			
I <sub>N</sub>	Current Noise Spectral Density			1.2		pA/√Hz			
HD2	2nd Harmonic Distortion (Note 3)			-70		dBc			
HD3	3rd Harmonic Distortion (Note 3)			-70		dBc			

NOTES:

1. Measured by moving the supplies from  $\pm 4V$  to  $\pm 6V$ 

2. Pulse test only and using a  $10\Omega$  load

3. Frequency = 1MHz,  $V_{OUT}$  =  $2V_{P\text{-}P}$  into 500  $\Omega$  and 5pF load

## $\label{eq:constraint} \textbf{Electrical Specifications} \qquad \mbox{V}_{S} + = +15\mbox{V}, \mbox{V}_{S} - = -15\mbox{V}, \mbox{T}_{A} = 25\mbox{°C}, \mbox{ } R_{F} = 180\mbox{$\Omega$}, \mbox{ } R_{G} = 20\mbox{$\Omega$}, \mbox{ } R_{L} = 500\mbox{$\Omega$} \mbox{ unless otherwise specified.}$

Parameter	Description	Conditions	Min	Тур	Max	Unit
DC PERFORM	ANCE					
V <sub>OS</sub>	Input Offset Voltage (SO8)			0.5	3	mV
	Input Offset Voltage (SOT23-5)				3	mV
T <sub>CVOS</sub>	Offset Voltage Temperature Coefficient			4.5		µV/°C
IB	Input Bias Current		-10	-7		μA
I <sub>OS</sub>	Input Bias Current Offset			0.12	0.7	μA
T <sub>CIB</sub>	Input Bias Current Temperature Coefficient			0.016		µA/°C
C <sub>IN</sub>	Input Capacitance			2.2		pF
A <sub>VOL</sub>	Open Loop Gain		80	90		dB
PSRR	Power Supply Rejection Ratio (Note 4)		65	80		dB
CMRR	Common Mode Rejection Ratio	at CMIR	70	85		dB
CMIR	Common Mode Input Range		-14.6		13.8	V
V <sub>OUTH</sub>	Positive Output Voltage Swing	No load, $R_F = 1k\Omega$	13.6	13.7		V
VOUTL	Negative Output Voltage Swing	No load, $R_F = 1k\Omega$		-13.8	-13.7	V
V <sub>OUTH2</sub>	Positive Output Voltage Swing	R <sub>L</sub> = 100Ω, R <sub>F</sub> = 1kΩ	10.2	11.2		V
V <sub>OUTL2</sub>	Negative Output Voltage Swing	R <sub>L</sub> = 100Ω, R <sub>F</sub> = 1kΩ		-10.3	-9.5	V
lout	Output Short Circuit Current (Note 5)		140	220		mA
I <sub>SY</sub>	Supply Current			5	6	mA
AC PERFORM	ANCE - R <sub>G</sub> = 20Ω, C <sub>L</sub> = 3pF					
BW	-3dB Bandwidth, $R_L = 500\Omega$			135		MHz
BW ±0.1dB	±0.1dB Bandwidth, $R_L = 500\Omega$			26		MHz
BW ±1dB	±1dB Bandwidth, $R_L = 500\Omega$			60		MHz
Peaking	Peaking, $R_L = 500\Omega$			2.1		dB
SR	Slew Rate (±2.5V Square Wave, Measured 25%-75%)		130	150		V/µS
OS	Overshoot, 4V <sub>P-P</sub> Output Square	Positive		1.6		%
	Wave	Negative		-4.4		%
Τ <sub>S</sub>	Settling Time to 0.1% of ±1V Pulse			48		ns



Parameter	Description	Conditions	Min	Тур	Max	Unit
V <sub>N</sub>	Voltage Noise Spectral Density			1.4		nV/√Hz
I <sub>N</sub>	Current Noise Spectral Density			1.1		pA/√Hz
HD2	2nd Harmonic Distortion (Note 6)			-72		dBc
HD3	3rd Harmonic Distortion (Note 6)			-73		dBc

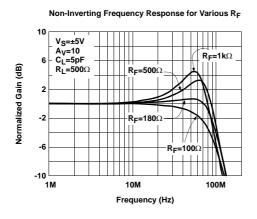
NOTES:

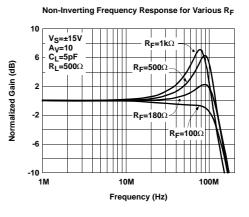
4. Measured by moving the supplies from  $\pm 13.5 \text{V}$  to  $\pm 16.5 \text{V}$ 

5. Pulse test only and using a  $10\Omega$  load

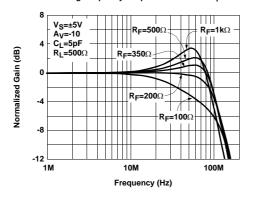
6. Frequency = 1MHz,  $V_{OUT}$  =  $2V_{P\mbox{-}P}$  into  $500\Omega$  and 5pF load

## **Typical Performance Curves**

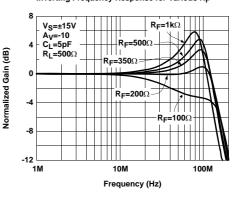


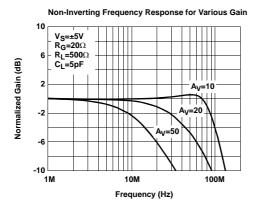


Inverting Frequency Response for Various RF

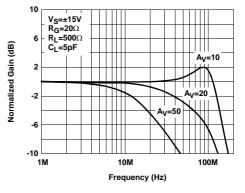


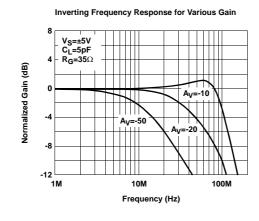
Inverting Frequency Response for Various R<sub>F</sub>

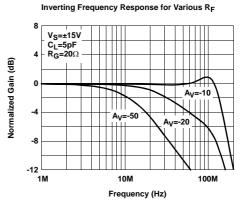


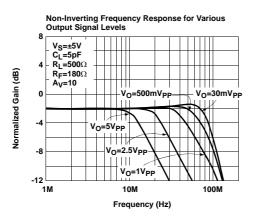


Non-Inverting Frequency Response for Various Gain

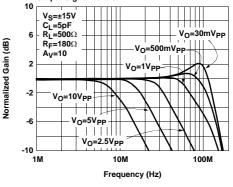


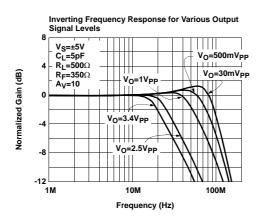






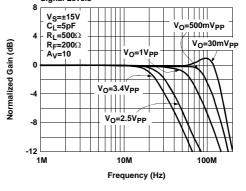
Non-Inverting Frequency Response for Various Output Signal Levels



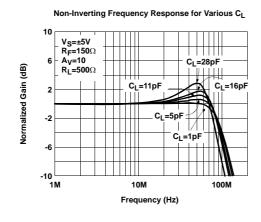


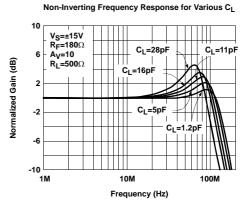
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Inverting Frequency Response for Various Output Signal Levels

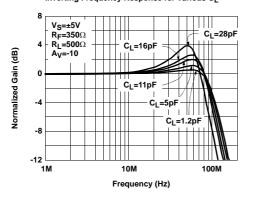


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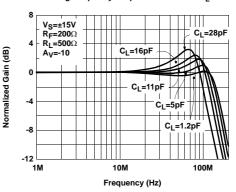


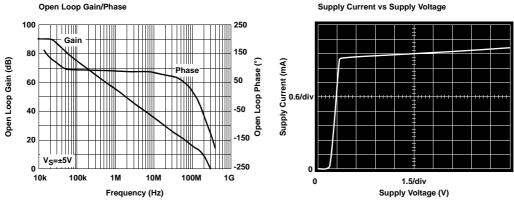


Inverting Frequency Response for Various CL

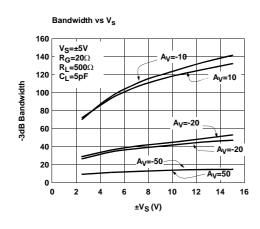


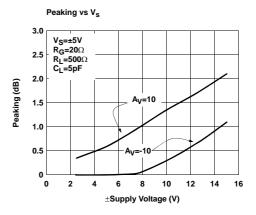
Inverting Frequency Response for Various CL

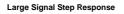


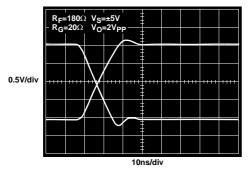


Supply Current vs Supply Voltage

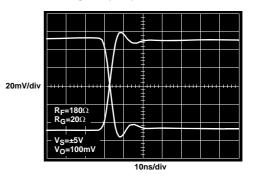


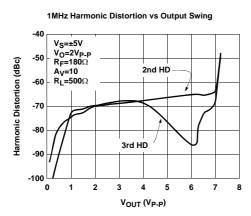




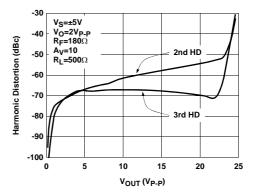


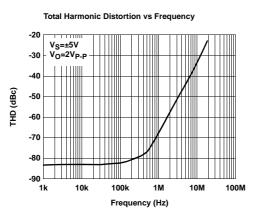
Small Signal Step Response

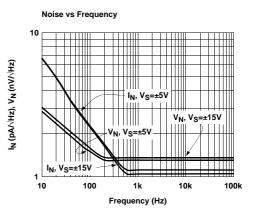


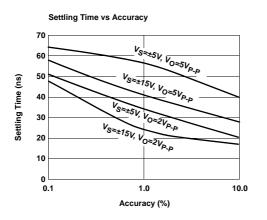


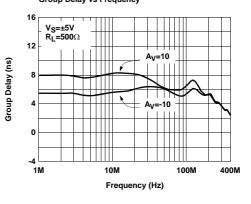
1MHz Harmonic Distortion vs Output Swing

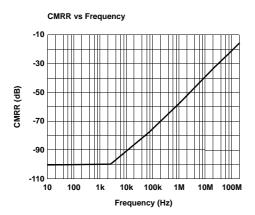


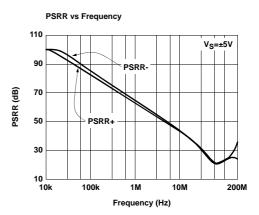




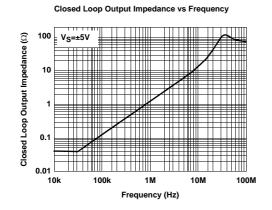


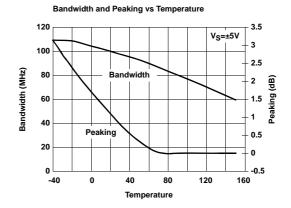


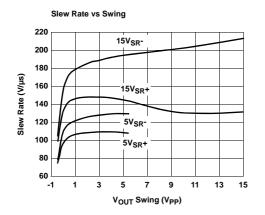


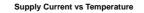


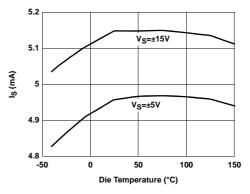
Group Delay vs Frequency

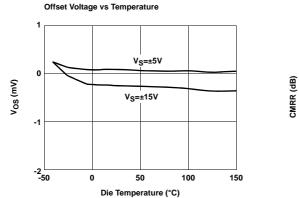




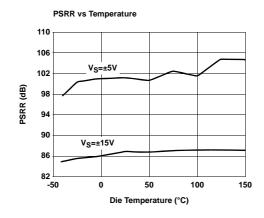


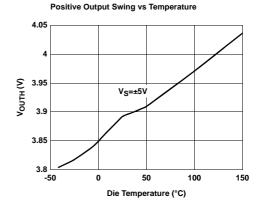


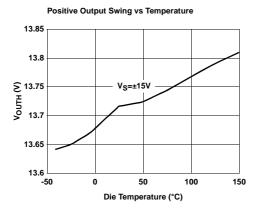




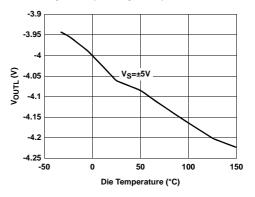
CMRR vs Temperature

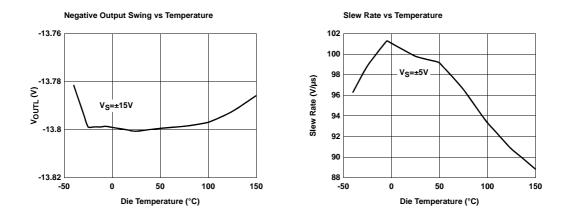


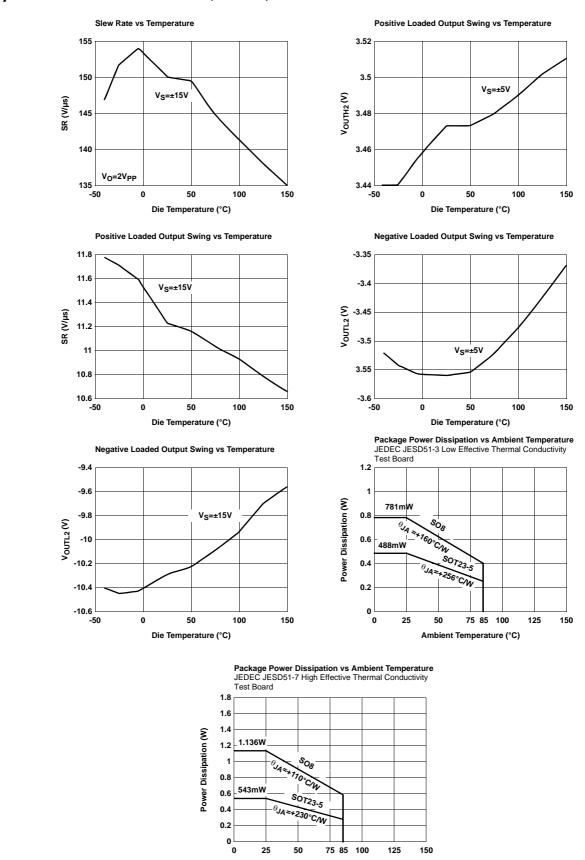




Negative Output Swing vs Temperature







Ambient Temperature (°C)

#### Typical Performance Curves (Continued)

EL2126	
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EL2126CW (5 ld SOT-23)	EL2126CS (8 ld SO)	Pin Name	Pin Function	Equivalent Circuit
1	6	VOUT	Output	VS+ Vout - Circuit 1
2	4	VS-	Supply	
3	3	VINA+	Input	$V_{IN^+} \leftarrow V_{S^+}$ $V_{S^-}$ Circuit 2
4	2	VINA-	Input	Reference Circuit 2
5	7	VS+	Supply	

## **Pin Descriptions**

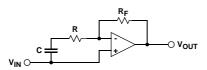
## Applications Information

#### **Product Description**

The EL2126 is an ultra-low noise, wideband monolithic operational amplifier built on Elantec's proprietary high speed complementary bipolar process. It features 1.3nV/ $\sqrt{Hz}$  input voltage noise, 200 $\mu$ V typical offset voltage, and 73dB THD. It is intended for use in systems such as ultrasound imaging where very small signals are needed to be amplified. The EL2126 also has excellent DC specifications: 200 $\mu$ V V<sub>OS</sub>, 22 $\mu$ A IB, 0.4 $\mu$ A I<sub>OS</sub>, and 106dB CMRR. These specifications allow the EL2126 to be used in DC-sensitive applications such as difference amplifiers.

#### Gain-Bandwidth Product

The EL2126 has a gain-bandwidth product of 650MHz at ±5V. For gains less than 20, higher-order poles in the amplifier's transfer function contribute to even higher closed-loop bandwidths. For example, the EL2126 has a -3dB bandwidth of 100MHz at a gain of 10 and decreases to 33MHz at gain of 20. It is important to note that the extra bandwidth at lower gain does not come at the expenses of stability. Even though the EL2126 is designed for gain  $\geq$  10. With external compensation, the device can also operate at lower gain settings. The RC network shown in Figure 1 reduces the feedback gain at high frequency and thus maintains the amplifier stability. R values must be less than RF divided by 9 and 1 divided by  $2\pi$ RC must be less than 200MHz.



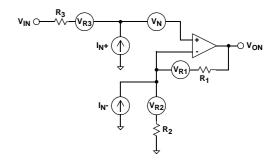


## Choice of Feedback Resistor, RF

The feedback resistor forms a pole with the input capacitance. As this pole becomes larger, phase margin is reduced. This increases ringing in the time domain and peaking in the frequency domain. Therefore, RF has some maximum value which should not be exceeded for optimum performance. If a large value of RF must be used, a small capacitor in the few pF range in parallel with RF can help to reduce this ringing and peaking at the expense of reducing the bandwidth. Frequency response curves for various RF values are shown in the typical performance curves section of this data sheet.

## Noise Calculations

The primary application for the EL2126 is to amplify very small signals. To maintain the proper signal-to-noise ratio, it is essential to minimize noise contribution from the amplifier. Figure 2 below shows all the noise sources for all the components around the amplifier.





V<sub>N</sub> is the amplifier input voltage noise

 $\mathsf{I}_N\mathsf{+}$  is the amplifier positive input current noise

 $I_{N}$ - is the amplifier negative input current noise

V<sub>RX</sub> is the thermal noise associated with each resistor:

$$V_{RX} = \sqrt{4kTRx}$$

where:

k is Boltzmann's constant =  $1.380658 \times 10^{-23}$ 

T is temperature in degrees Kelvin (273+ °C)

The total noise due to the amplifier seen at the output of the amplifier can be calculated by using the Equation 2.

As the equation shows, to keep noise at a minimum, small resistor values should be used. At higher amplifier gain configuration where  $R_2$  is reduced, the noise due to IN-,  $R_2$ , and  $R_1$  decreases and the noise caused by IN+, VN, and  $R_3$  starts to dominate. Because noise is summed in a root-mean-squares method, noise sources smaller than 25% of the largest noise source can be ignored. This can greatly simplify the formula and make noise calculation much easier to calculate.

$$V_{ON} = \sqrt{BW} \times \sqrt{\left(VN^2 \times \left(1 + \frac{R_1}{R_2}\right)^2 + IN^2 \times R_1^2 + IN^2 \times R_3^2 \times \left(1 + \frac{R_1}{R_2}\right)^2 + 4 \times K \times T \times R_1 + 4 \times K \times T \times R_2 \times \left(\frac{R_1}{R_2}\right)^2 + 4 \times K \times T \times R_3 \times \left(1 + \frac{R_1}{R_2}\right)^2\right)}$$
(EQ. 2)

(EQ. 1)

## **Output Drive Capability**

The EL2126 is designed to drive low impedance load. It can easily drive  $6V_{P-P}$  signal into a  $100\Omega$  load. This high output drive capability makes the EL2126 an ideal choice for RF, IF, and video applications. Furthermore, the EL2126 is current-limited at the output, allowing it to withstand momentary short to ground. However, the power dissipation with output-shorted cannot exceed the power dissipation capability of the package.

## Driving Cables and Capacitive Loads

Although the EL2126 is designed to drive low impedance load, capacitive loads will decreases the amplifier's phase margin. As shown in the performance curves, capacitive load can result in peaking, overshoot and possible oscillation. For optimum AC performance, capacitive loads should be reduced as much as possible or isolated with a series resistor between  $5\Omega$  to  $20\Omega$ . When driving coaxial cables, double termination is always recommended for reflection-free performance. When properly terminated, the capacitance of the coaxial cable will not add to the capacitive load seen by the amplifier.

## Power Supply Bypassing And Printed Circuit Board Layout

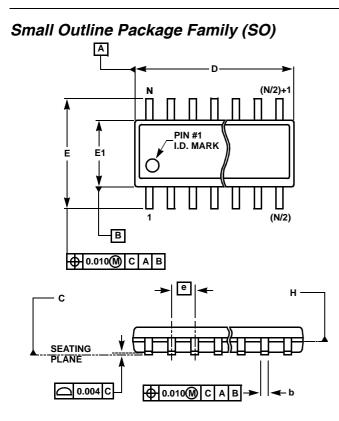
As with any high frequency devices, good printed circuit board layout is essential for optimum performance. Ground plane construction is highly recommended. Lead lengths should be kept as short as possible. The power supply pins must be closely bypassed to reduce the risk of oscillation. The combination of a 4.7µF tantalum capacitor in parallel with 0.1µF ceramic capacitor has been proven to work well when placed at each supply pin. For single supply operation, where pin 4 (V<sub>S</sub>-) is connected to the ground plane, a single 4.7µF tantalum capacitor in parallel with a 0.1µF ceramic capacitor across pins 7 (V<sub>S</sub>+) and pin 4 (V<sub>S</sub>-) will suffice.

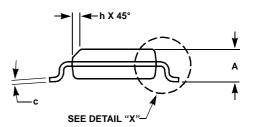
For good AC performance, parasitic capacitance should be kept to a minimum. Ground plane construction again should be used. Small chip resistors are recommended to minimize series inductance. Use of sockets should be avoided since they add parasitic inductance and capacitance which will result in additional peaking and overshoot.

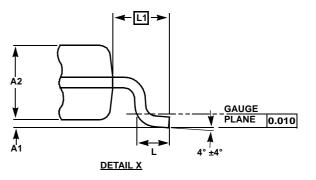
## Supply Voltage Range and Single Supply Operation

The EL2126 has been designed to operate with supply voltage range of  $\pm 2.5V$  to  $\pm 15V$ . With a single supply, the EL2126 will operate from  $\pm 5V$  to  $\pm 30V$ . Pins 4 and 7 are the power supply pins. The positive power supply is connected to pin 7. When used in single supply mode, pin 4 is connected to ground. When used in dual supply mode, the negative power supply is connected to pin 4.

As the power supply voltage decreases from +30V to +5V, it becomes necessary to pay special attention to the input voltage range. The EL2126 has an input voltage range of 0.4V from the negative supply to 1.2V from the positive supply. So, for example, on a single +5V supply, the EL2126 has an input voltage range which spans from 0.4V to 3.8V. The output range of the EL2126 is also quite large, on a +5V supply, it swings from 0.4V to 3.8V.







#### **MDP0027**

SMALL OUTLINE PACKAGE FAMILY (SO)

		INCHES							
NOTES	TOLERANCE	SO28 (SOL-28)	SO24 (SOL-24)	SO20 (SOL-20)	SO16 (0.300") (SOL-16)	SO16 (0.150")	SO-14	SO-8	SYMBOL
-	MAX	0.104	0.104	0.104	0.104	0.068	0.068	0.068	А
-	±0.003	0.007	0.007	0.007	0.007	0.006	0.006	0.006	A1
-	±0.002	0.092	0.092	0.092	0.092	0.057	0.057	0.057	A2
-	±0.003	0.017	0.017	0.017	0.017	0.017	0.017	0.017	b
-	±0.001	0.011	0.011	0.011	0.011	0.009	0.009	0.009	С
1, 3	±0.004	0.704	0.606	0.504	0.406	0.390	0.341	0.193	D
-	±0.008	0.406	0.406	0.406	0.406	0.236	0.236	0.236	E
2, 3	±0.004	0.295	0.295	0.295	0.295	0.154	0.154	0.154	E1
-	Basic	0.050	0.050	0.050	0.050	0.050	0.050	0.050	е
-	±0.009	0.030	0.030	0.030	0.030	0.025	0.025	0.025	L
-	Basic	0.056	0.056	0.056	0.056	0.041	0.041	0.041	L1
-	Reference	0.020	0.020	0.020	0.020	0.013	0.013	0.013	h
-	Reference	28	24	20	16	16	14	8	Ν

NOTES:

1. Plastic or metal protrusions of 0.006" maximum per side are not included.

2. Plastic interlead protrusions of 0.010" maximum per side are not included.

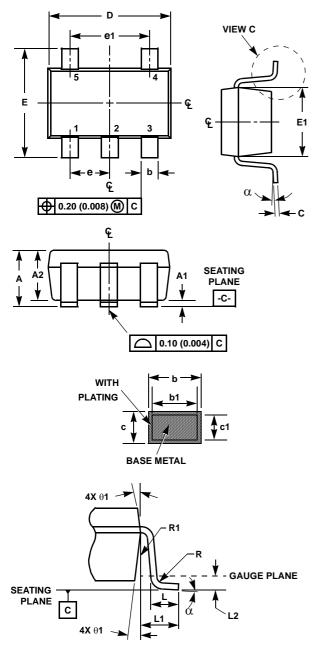
3. Dimensions "D" and "E1" are measured at Datum Plane "H".

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4. Dimensioning and tolerancing per ASME Y14.5M-1994

## EL2126

## Small Outline Transistor Plastic Packages (SOT23-5)



VIEW C

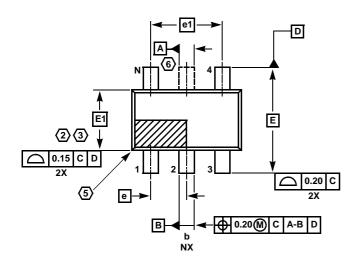
	INC	HES	MILLIN	IETERS	
SYMBOL	MIN	MAX	MIN	MAX	NOTES
А	0.036	0.057	0.90	1.45	-
A1	0.000	0.0059	0.00	0.15	-
A2	0.036	0.051	0.90	1.30	-
b	0.012	0.020	0.30	0.50	-
b1	0.012	0.018	0.30	0.45	
С	0.003	0.009	0.08	0.22	6
c1	0.003	0.008	0.08	0.20	6
D	0.111	0.118	2.80	3.00	3
Е	0.103	0.118	2.60	3.00	-
E1	0.060	0.067	1.50	1.70	3
е	0.037	4 Ref	0.95	5 Ref	-
e1	0.074	8 Ref	1.90	) Ref	-
L	0.014	0.022	0.35	0.55	4
L1	0.024	Ref.	0.60	Ref.	
L2	0.010	) Ref.	0.25 Ref.		
Ν	Ę	5	5		5
R	0.004	-	0.10	-	
R1	0.004	0.010	0.10	0.25	
α	0 <sup>0</sup>	8 <sup>0</sup>	0 <sup>0</sup>	8 <sup>0</sup>	-

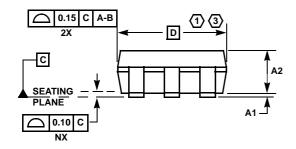
NOTES:

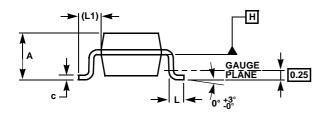
Rev. 2 9/03

- 1. Dimensioning and tolerance per ASME Y14.5M-1994.
- 2. Package conforms to EIAJ SC-74 and JEDEC MO178AA.
- 3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.
- 4. Footlength L measured at reference to gauge plane.
- 5. "N" is the number of terminal positions.
- 6. These Dimensions apply to the flat section of the lead between 0.08mm and 0.15mm from the lead tip.
- 7. Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.

## SOT-23 Package Family







MDP0038

SOT-23 PACKAGE FAMILY

	MILLIN		
SYMBOL	SOT23-5	SOT23-6	TOLERANCE
А	1.45	1.45	MAX
A1	0.10	0.10	±0.05
A2	1.14	1.14	±0.15
b	0.40	0.40	±0.05
С	0.14	0.14	±0.06
D	2.90	2.90	Basic
E	2.80	2.80	Basic
E1	1.60	1.60	Basic
е	0.95	0.95	Basic
e1	1.90	1.90	Basic
L	0.45	0.45	±0.10
L1	0.60	0.60	Reference
Ν	5	6	Reference
	1		Rev. F 2/07

NOTES:

- 1. Plastic or metal protrusions of 0.25mm maximum per side are not included.
- Plastic interlead protrusions of 0.25mm maximum per side are not included.
- 3. This dimension is measured at Datum Plane "H".
- 4. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 5. Index area Pin #1 I.D. will be located within the indicated zone (SOT23-6 only).
- 6. SOT23-5 version has no center lead (shown as a dashed line).

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